



PINGWEI ENTERPRISE

1N914, 1N4148 THRU 1N4454

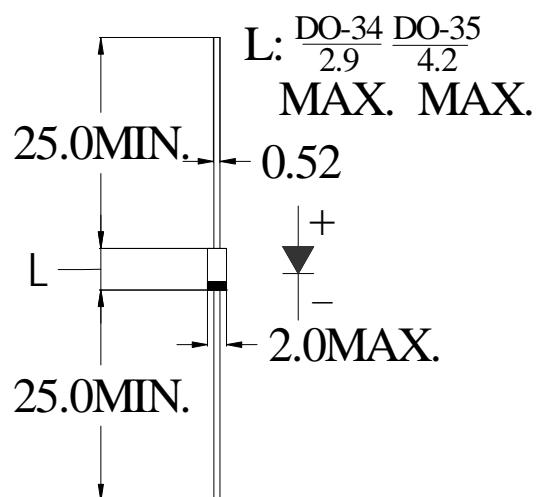
HIGH SPEED SWITCHING DIODES

FEATURES

- Silicon epitaxial planar diodes
- Low power loss, high efficiency
- Low leakage
- Low forward voltage
- High speed switching
- High current capability
- High reliability

MECHANICAL DATA

- Case: Glass sealed case
- Lead: MIL-STD- 202E, Method 208 guaranteed
- Polarity: Color band denotes cathode end
- Mounting position: Any
- Weight: 0.13 gram

DO-34 & DO-35

Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND ELECTRONICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified. Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Type Number	SYMBOL	1N914	1N4148	1N4150	1N4151	1N4154	1N4448	1N4454	units
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	100	100	50	75	35	100	75	V
Maximum Average rectified Current	$I_{F(AV)}$	75	150	200	150	150	150	150	mA
Maximum power dissipation $t_{amb}=25^{\circ}\text{C}$	P_{tot}	250	500	500	500	500	500	500	mW
Maximum Forward Voltage	V_F	1.0/10	1.0/10	1.0/200	1.0/150	1.0/300	1.0/10	1.0/10	V/mA
Maximum reverse current	I_R	25/20	5000/75	100/50	50/50	100/25	5000/75	100/10	nA/V
Maximum reverse recovery time	t_{rr}	4.0	4.0	4.0	2.0	2.0	4.0	4.0	nS
Maximum junction capacitance	C_J					4.0			pF
Storage Temperature	T_{STG}				-55 to +175				°C
Operation Junction Temperature	T_J				-55 to +175				°C

Note: 1. 1N914A, 1N914B is same as 1N914, except different forward voltage:

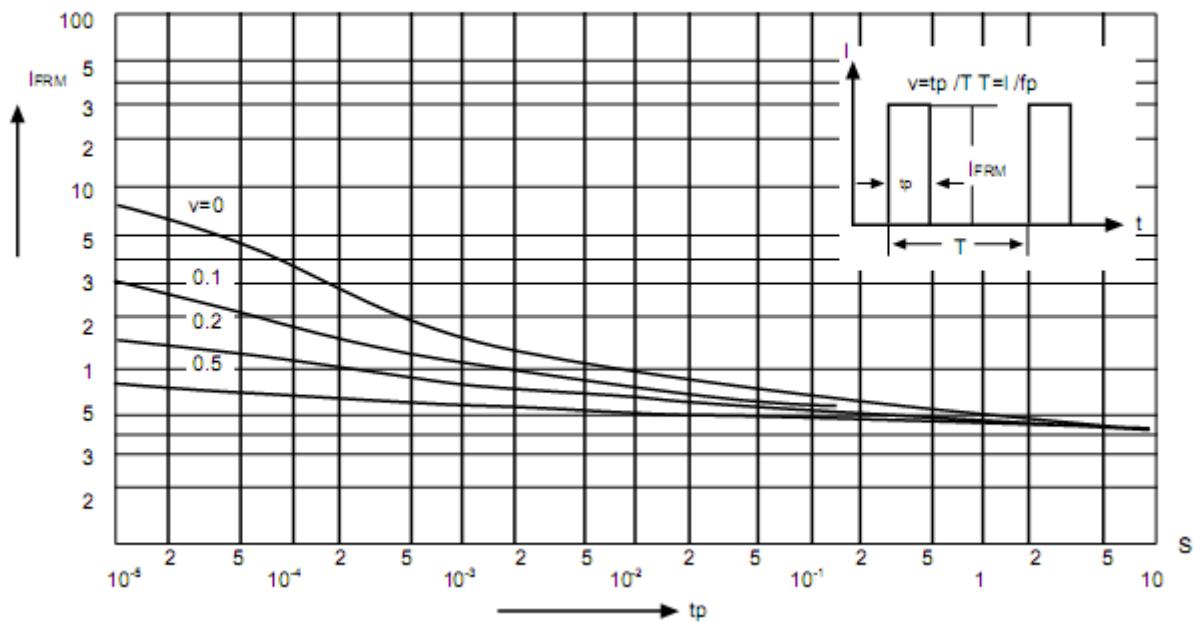
1N914A-1.0/20 V/mA

1N914B-1.0/100 V/mA

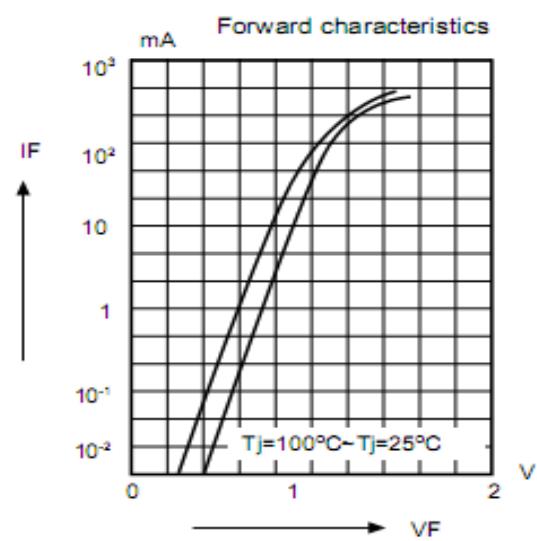
2. Suffix "M" stands for "DO-34" package. (e.g.: 1N4148M)

RATING AND CHARACTERISTIC CURVES (1N914, 1N4148 THRU 1N4454)

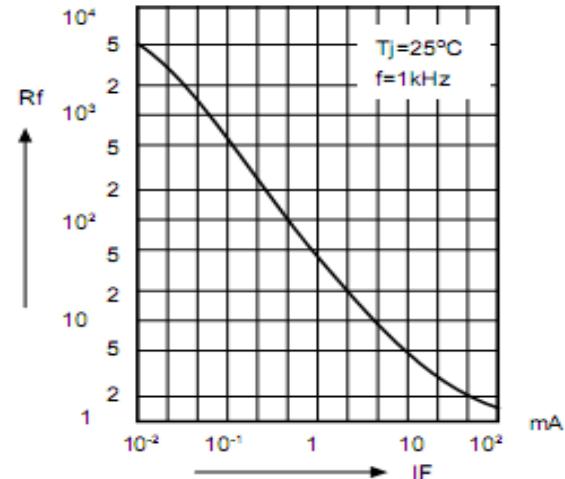
A Admissible repetitive peak forward current versus pulse duration



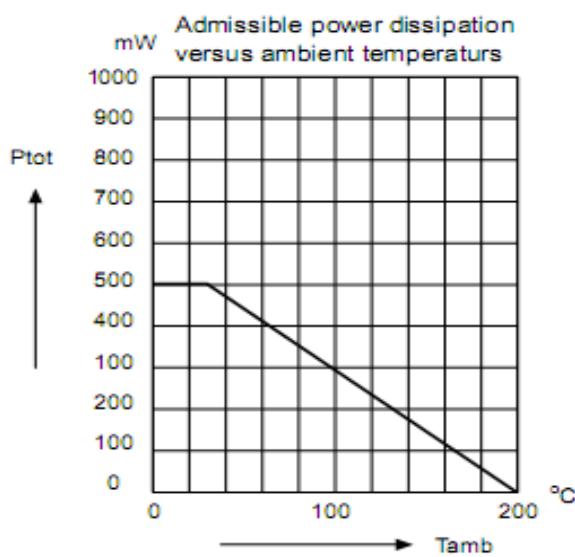
Forward characteristics



Dynamic forward resistance Ω versus forward current



Admissible power dissipation versus ambient temperature



Relative capacitance versus reverse voltage

